



SONNENSCHN, NATH & ROSENTHAL
8000 Sears Tower
233 S. Wacker Drive
Chicago, IL 60606
312/876-0200

AF/2814

APPLICANTS: Mitsuhiko Nakamura et al. OLD DOCKET NO.: P97,0322
NEW DOCKET NO.: 09794353-0005
SERIAL NO. 08/809,463 GROUP ART UNIT: 2814
FILING DATE: July 18, 1997 EXAMINER: P. Cao
INVENTION: "MULTI-LAYERED STRUCTURE FOR FABRICATING AN OHMIC
ELECTRODE AND OHMIC ELECTRODE"

AMENDMENT AFTER FINAL

Hon. Assistant Commissioner of Patents
Washington D.C. 2023

SIR:

Transmitted herewith is an amendment in the above-identified application.

Additional claim fee is required.

The fee has been calculated as shown below.

RECEIVED
APR 22 2003
TECHNOLOGY CENTER 2800

CLAIMS AS AMENDED						
	(2) CLAIMS REMAINING AFTER AMENDMENT		(4) HIGHEST NO. PREVIOUSLY PAID FOR	(5) PRESENT EXTRA	(6) RATE	(7) ADDITIONAL FEE
TOTAL CLAIMS	19	MINUS	20	-0-	() X 9.00 () X 18.00	0.00
INDEP. CLAIMS	4	MINUS	4	-0-	() X 39.00 () X 80.00	0.00
Application amended to contain any multiple dependent claims not previously paid for.				() YES (X) NO	() \$135.00 () \$270.00 ONE TIME	
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00	

- Applicant petitions the Commissioner of Patents and Trademarks to extend this time for response to the Office Action dated _____ for ____ month so that the period for response is extended to _____.
- The Commissioner is hereby authorized to charge the amount of \$_____ to Attorney firm's American Express account no. to cover the extension of time fee. A duplicate of this sheet is enclosed.
- A check in the amount of \$____ is attached to cover the additional claim fee.
- ☒ The Commissioner is hereby authorized to charge any additional fees which may be required, or to credit any overpayment to account No. 19-3140. A duplicate of this sheet is enclosed.
- When phoning re this application, please call 312/876-8000 - Ext. 2606.

SONNENSCHN NATH & ROSENTHAL

DATE: April 15, 2003

BY Christopher P. Rauch (Reg. No. 45,034)
Christopher P. Rauch

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited as first class mail in an envelope addressed to BOX AF, Asst. Commissioner of Patents, Washington, D.C. 20231 on April 15, 2003.

Christopher P. Rauch
Christopher P. Rauch



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Mitsuhiro Nakamura et al. OLD DOCKET NO.: P97,0322
NEW DOCKET NO.: 09794353-0005
SERIAL NO. 08/809,463 GROUP ART UNIT: 2814
FILING DATE: July 18, 1997 EXAMINER: P. Cao
INVENTION: "MULTI-LAYERED STRUCTURE FOR FABRICATING
OHMIC ELECTRODE AND OHMIC ELECTRODE"

AMENDMENT AFTER FINAL

Hon. Assistant Commissioner for Patents
Washington, DC 20231

S I R:

This Amendment After Final is filed in response to the Office Action of January 16, 2003.

Please reconsider the application in view of the amendment and remarks presented below.

IN THE CLAIMS

Please amend claims 1, 9, 10, and 19 as follows:

1. (Three Times Amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiSiN film, and a TiON film.

9. (Three Times Amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiSiN film, and a TiON film.

34D Audit
E M. Bauman
APR 22 2003
RECEIVED
TECHNOLOGY CENTER 2800
4/24/03

PLEASE DO NOT ENTER
PC
4/28/03